

Amendments to the Specification:

Please amend the page 7, the paragraph beginning at line 16 to recite:

In accordance with the present invention, recesses 2 such as troughs and vias are provided on at least one major surface of a semiconductor substrate 13 [[not shown]]. Typical semiconductor substrates include silicon and group III-V semiconductors. Electrical insulation 3 is provided over the major surface and in the recesses such as silicon dioxide which can be thermally grown or deposited such as by chemical vapor deposition or physical vapor deposition. Typically, the insulating layer is about 2000 to about 30,000 Å thick, and more typically about 4000 to about 20,000 Å thick.